LH5762/J

CMOS 64K (8K × 8) OTPROM/EPROM

FEATURES

- 8,192 × 8 bit organization
- Access times:
  LH5762J: 55/70 ns (MAX.)
  LH5762: 70 ns (MAX.)
- Single +5 V power supply
- Low power consumption:
  Operating: 394 mW (MAX.)
  Standby: 78.75 mW (MAX.)
- Fully static operation
- Three-state outputs
- TTL compatible I/O
- High speed programming:
  Compatible to INTEL intelligent programming™ algorithm
  (32 second programming)
- Pin compatible with the i2764
- Packages:
  EPROM
  28-pin, 600-mil CERDIP
  OTPROM
  28-pin, 600-mil DIP
- JEDEC standard pinout

DESCRIPTION

The LH5762J is a high-performance 64K, UV erasable, electrically programmable read-only-memory, organized as 8,192 × 8 bits. It is manufactured in an advanced CMOS technology, which allows it to operate at Bipolar speeds while consuming only 75 mA.

The LH5762J has very high output drive capability. It can source 4 mA and sink 16 mA per output.

The LH5762J is configured in the standard EPROM pinout which provides an easy upgrade path for systems that are currently using standard EPROMs.

The LH5762 is a one-time PROM packaged in plastic DIP.

PIN CONNECTIONS

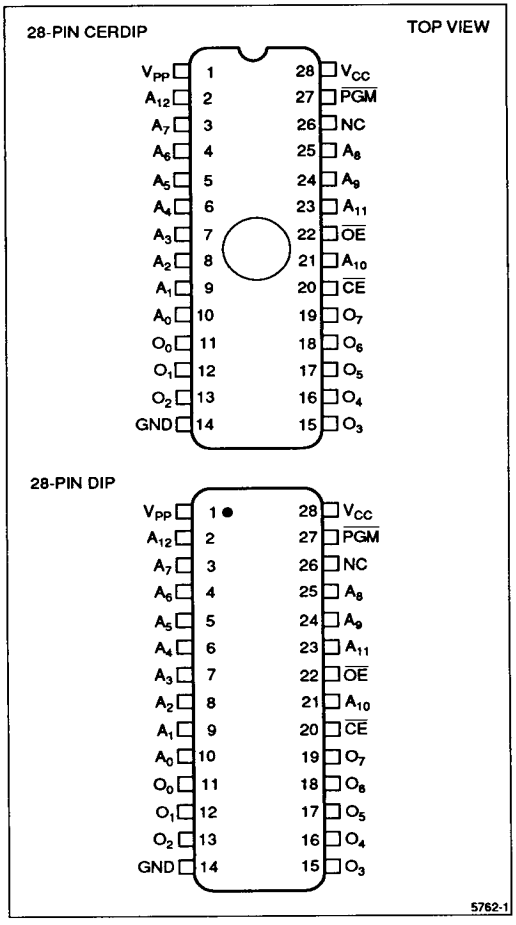

Figure 1. Pin Connections for CERDIP and DIP Packages

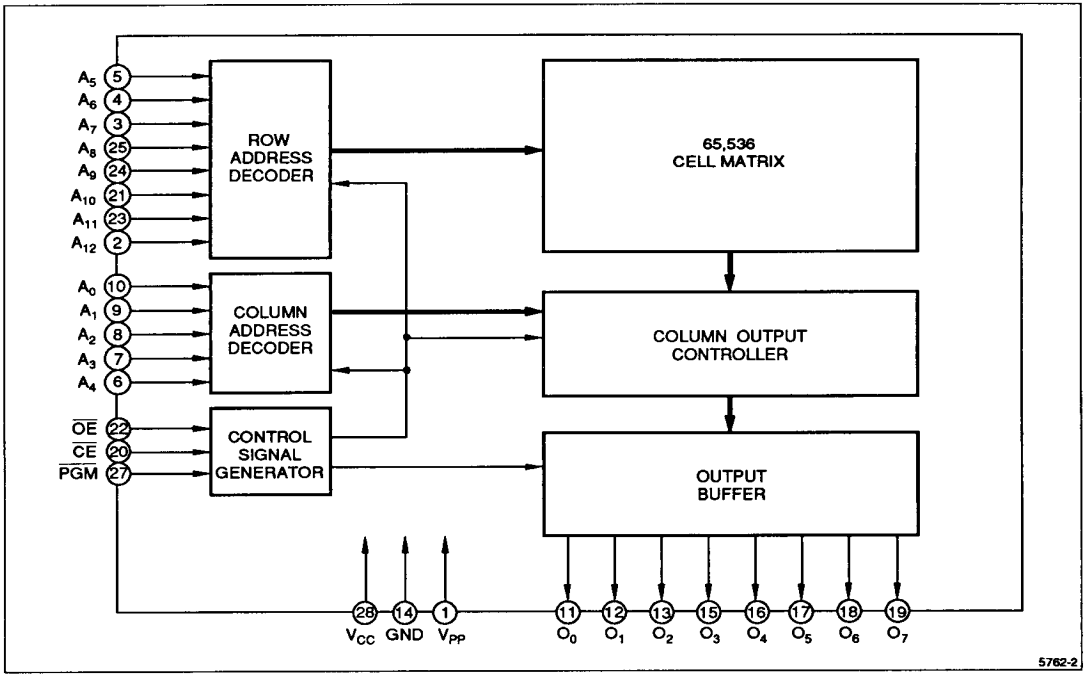

Figure 2. LH5762/J Block Diagram

PIN DESCRIPTION

SIGNAL	PIN NAME	NOTE
A_0 - A_{12}	Address input	
O_0 - O_7	Data output (input)	1
$\overline{CE}$	Chip Enable input	
$\overline{OE}$	Output Enable input	
$\overline{PGM}$	Program input	

SIGNAL	PIN NAME	NOTE
V_{PP}	Program power	
V_{CC}	Power supply	
GND	Ground	
NC	Non connection	

NOTE:
1. O_0 - O_7 pins are also used to input data to the column output controller through input buffers in programming mode.

TRUTH TABLE

MODE		O_0 - O_7	$\overline{CE}$	$\overline{OE}$	$\overline{PGM}$	V_{CC}	V_{PP}
Read	Read	Data out	L	L	H	+5 V	+5 V
	Output disable	High-Z	L	H	H	+5 V	+5 V
	Standby	High-Z	H	X	X	+5 V	+5 V
Program	Program	Data in	L	H	L	+6 V	+12.5 V
	Program verify	Data out	L	L	H	+6 V	+12.5 V
	Program inhibit	High-Z	H	X	X	+6 V	+12.5 V

NOTE:
X = H or L, H = V_{IH}, L = V_{IL}

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	NOTE
Supply voltage	V_{CC}	-0.6 to +7.0	V	1
	V_{PP}	-0.6 to +13.5		
	V_{IN}, V_{OUT}	-0.6 to +7.0		
Operating temperature	Topr	0 to +70	°C	
Storage temperature	Tstg	-65 to +150	°C	2
		-55 to +150		3

NOTES:
1. The maximum applicable voltage on any pin with respect to GND.
   Maximum ratings are those values beyond which damage to the device may occur.
2. Applied to ceramic package.
3. Applied to plastic package.

RECOMMENDED OPERATING CONDITIONS (Read Mode) (T_A = 0 to +70°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	V_{CC}	4.75	5.0	5.25	V
	V_{PP}	4.75	5.0	5.25	
Input "Low" voltage	V_{IL}	-0.1		0.8	V
Input "High" voltage	V_{IH}	2.0		V_{CC} +0.3	V

DC CHARACTERISTICS (Read Mode) (V_{CC} = 5 V ± 5%, V_{PP} = V_{CC}, T_A = 0 to +70°C)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Input leakage current	I_{LI}	V_{IN} = GND or V_{CC}	-10		10	µA	
Output leakage current	I_{LO}	V_{OUT} = GND or V_{CC}	-10		10	µA	
V_{PP} supply current	I_{PP}	V_{PP} = V_{CC}			100	µA	
V_{PP} pin voltage	V_{PP}		V_{CC} - 0.4		V_{CC}	V	
V_{CC} standby current	I_{SB1}	$\overline{CE}$ = V_{CC} ± 0.3 V, CMOS input			15	mA	
	I_{SB2}	$\overline{CE}$ = V_{IH}, TTL input			20	mA	
V_{CC} operating current	I_{CC1}	$\overline{CE}$ = GND ± 0.3 V			75	mA	1, 2
	I_{CC2}	$\overline{CE}$ = V_{IL}			75	mA	1, 3
Input "Low" voltage	V_{IL}		-0.1		0.8	V	
Input "High" voltage	V_{IH}		2.0		V_{CC} + 0.3	V	
Output "Low" voltage	V_{OL}	I_{OL} = 16 mA			0.45	V	
Output "High" voltage	V_{OH}	I_{OH} = -4 mA	2.4			V	

NOTES:
1. Minimum cycle time, I_{OUT} = 0 mA
2. CMOS input: V_{IN} = GND ± 0.3 V, or V_{CC} ± 0.3 V
3. TTL input: V_{IN} = V_{IL} or V_{IH}

AC CHARACTERISTICS (Read Mode) (V_{CC} = V_{PP} = 5 V ± 5%, T_A = 0 to +70°C)

PARAMETER	SYMBOL	LH5762J-55		LH5762J-70 LH5762-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Address to output delay	t_{ACC}		55		70	ns
$\overline{CE}$ to output delay	t_{CE}		55		70	ns
$\overline{OE}$ to output delay	t_{OE}		25		25	ns
Output enable high to output float	t_{DF}	0	20	0	25	ns
Address to output hold	t_{OH}	10		10		ns

AC TEST CONDITIONS

PARAMETER	RATING
Input voltage amplitude	0 V to 3 V
Input rise/fall time	≤ 10 ns
Input reference level	1 V, 2 V
Output reference level	0.8 V, 2 V

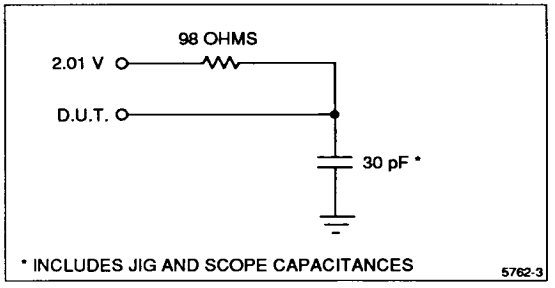

Figure 3. Output Load Circuit

CAPACITANCE (T_A = 25°C, f = 1MHz)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input capacitance	C_{IN}	V_{IN} = 0 V		4	6	pF
Output capacitance	C_{OUT}	V_{OUT} = 0 V		8	12	pF

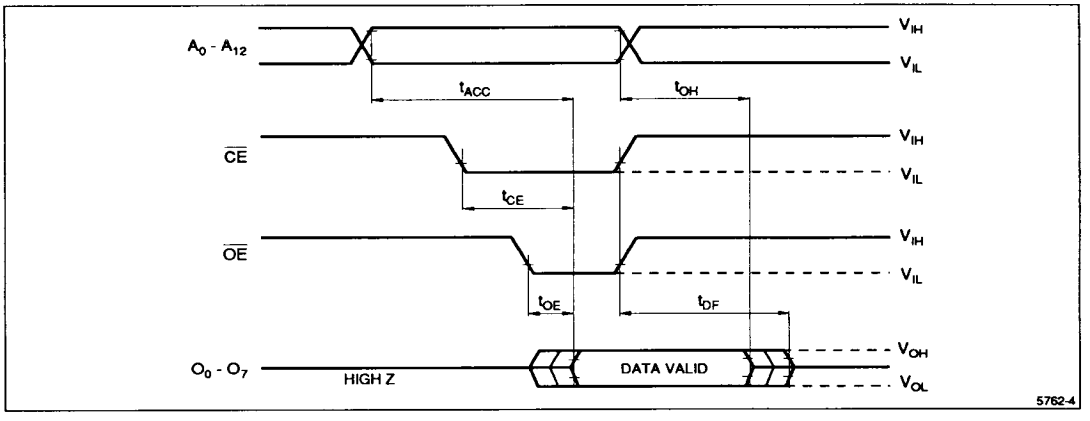

Figure 4. Timing Diagram (Read Mode)

RECOMMENDED OPERATING CONDITIONS (Program Mode) (T_A = 25°C ± 5°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	V_{CC}	5.75	6.0	6.25	V
	V_{PP}	12.2	12.5	12.8	
Input voltage	V_{IL}	-0.1		0.45	V
	V_{IH}	2.4		V_{CC} + 0.3	

DC CHARACTERISTICS (Program Mode)

(V_{CC} = 6.0 V ± 0.25 V, V_{PP} = 12.5 V ± 0.3 V, T_A = 25°C ± 5°C)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input leakage current	I_{LI}	V_{IN} = V_{CC} or 0.45 V	-10		10	µA
V_{CC} supply current	I_{CC}				75	mA
V_{PP} supply current	I_{PP}	$\overline{CE}$ = $\overline{PGM}$ = V_{IL}			50	mA
Input "Low" voltage	V_{IL}		-0.1		0.45	V
Input "High" voltage	V_{IH}		2.4		V_{CC} + 0.3	V
Output "Low" voltage	V_{OL}	I_{OL} = 16 mA			0.45	V
Output "High" voltage	V_{OH}	I_{OH} = -4 mA	2.4			V

AC CHARACTERISTICS (Program Mode)

(V_{CC} = 6.0 V ± 0.25 V, V_{PP} = 12.5 V ± 0.3 V, T_A = 25°C ± 5°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Address setup time	t_{AS}	2			µs	
Chip enable setup time	t_{CES}	2			µs	
Output enable setup time	t_{OES}	2			µs	
Data setup time	t_{DS}	2			µs	
Address hold time	t_{AH}	0			µs	
Data hold time	t_{DH}	2			µs	
Chip enable to output float delay	t_{DF}	0		150	ns	
Data valid from output enable	t_{OE}			150	ns	
V_{PP} setup time	t_{VPS}	2			µs	
V_{CC} setup time	t_{VCS}	2			µs	
$\overline{PGM}$ pulse width	t_{PW}	0.95	1.0	1.05	ms	
Add $\overline{PGM}$ pulse width	t_{OPW}	2.85		78.75	ms	1
Program pulse count	N	1		25	TIMES	

NOTE:
1. This width is defined by the Program Flowchart (Figure 6).

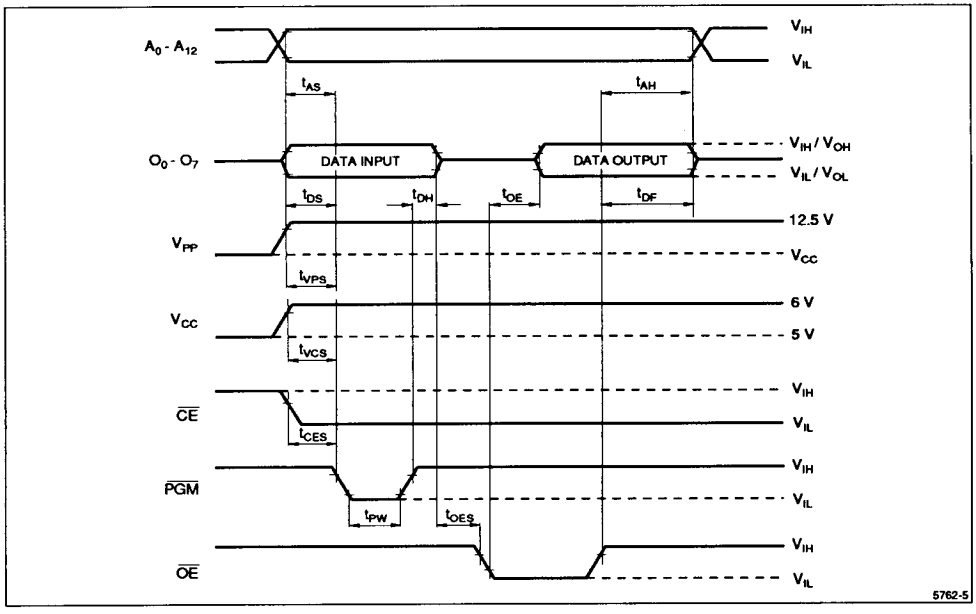

Figure 5. Timing Diagram (Program Mode)

PROGRAMMING

Upon delivery from SHARP or after each erasure (see erasure section), the LH5762 and LH5762J have all 8,192 × 8 bits in the "1", or high state. "0's" are loaded into the LH5762 and LH5762J through the procedure of programming.

The programming mode is entered when +12.5 V is applied to the V_{PP} pin and $\overline{CE}$ is at V_{IL}. A 0.1 µF capacitor between V_{PP} and GND is needed to prevent excessive voltage transients, which could damage the device. The address to be programmed is applied to the proper address pins. 8-bit patterns are placed on the respective data pins. The voltage levels should be standard TTL levels.

ERASURE

In order to clear all locations of their programmed contents, it is necessary to expose the LH5762J to an ultra-violet light source. A dosage of 15 W-second/cm^2 is required to completely erase an LH5762J. This dosage can be obtained by exposure to an ultra-violet lamp (wave-length of 2,537 Angstroms (Å)) with intensity of 12,000 µW/cm^2 for 20 to 30 minutes. The LH5762J should be about one inch from the source and all filters should be removed from the UV light source prior to erasure.

It is important to note that the LH5762J and similar devices, will erase with light sources having wavelength shorter than 4,000 Å.

Although erasure times will be much longer than with UV sources at 2,537 Å, the exposure to fluorescent light and sunlight will eventually erase the LH5762J. Exposure to them should be prevented to realize maximum system reliability. If used in such an environment, the package windows should be covered by an opaque label or substance.

CAUTION

Fluorescent light and sunlight contain UV rays which will erase the EPROM. To prevent deterioration of EPROM data due to UV rays, it is recommended that EPROMs should not be left under direct sunlight or fluorescent light, or the package window should be covered with an opaque material.

Care must be taken to avoid friction between package window and plastics or the like, as the resulting static-electric build-up may cause faulty operation.

1. V_{CC} must be applied either coincidently or before V_{PP} and removed either coincidently or after V_{PP}.

2. V_{PP} must not be greater than 13.5 volts including overshoot.

3. During $\overline{CE} = \overline{PGM} = V_{IL}$, V_{PP} must not be switched from 5 volts to 12.5 volts or vice-versa.

4. Removing or inserting the device while 12.5 volts is supplied may harm the reliability of the device.

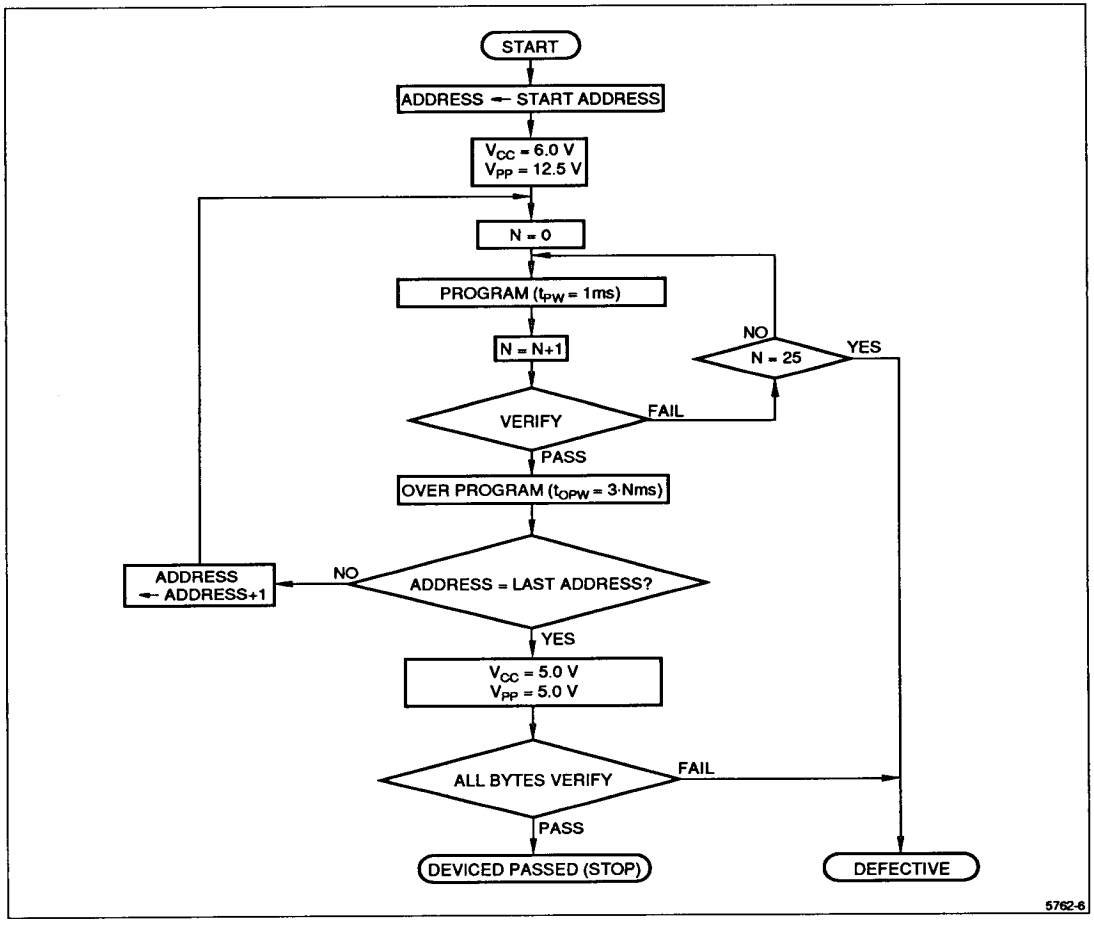

Figure 6. Programming Flowchart

ORDERING INFORMATION